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Complete if Known

Application Number	10/081439
Filing Date	February 20, 2002
First Named Inventor	Ahn, Kie
Group Art Unit	2818
Examiner Name	Unknown

Sheet 1 of 1

Attorney Docket No: 01303.046US1

US PATENT DOCUMENTS

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DAS		GELLER, S., et al., "Crystallographic Studies of Perovskite-like Compounds. II. Rare Earth Aluminates", <u>Acta Cryst.</u> , Vol. 9, (1956), pp. 1019-1025	
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		LEE, A.E., et al., "Epitaxially grown sputtered LaAlO ₃ films", <u>Appl. Phys. Lett.</u> , 57 (19), (November 5, 1990), pp. 2019-2021	
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		PARK, BYUNG-EUN, et al., "Electrical properties of LaAlO ₃ /Si and Sr _{0.8} Bi ₂ Ta ₂ O ₉ /LaAlO ₃ /Si structures", <u>Applied Physics Letters</u> , Vol. 79, No. 6, (August 6, 2001), pp. 806-808	
		TAKEMOTO, J.H., et al., "Microstrip Resonators and Filters Using High-TC Superconducting Thin Films on LaAlO ₃ ", <u>IEEE Transaction on Magnetics</u> , Vol. 27, No. 2, (March, 1991), pp. 2549-2552	
		WILK, G.D., et al., "High-gate dielectrics: Current status and materials properties considerations", <u>J. Appl. Phys.</u> , Vol. 89, No. 10, (May 15, 2001), pp. 5243-5275	

not provided

EXAMINER

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